

N-channel TrenchMOS logic level FET 19 March 2014

Product data sheet

1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for logic level gate drive sources

3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- Motors, lamps and solenoids

4. Quick reference data

Table 1. C	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	-	55	V
I _D	drain current	V _{GS} = 5 V; T _{sp} = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	5.5	А
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>	-	-	8	W
Static char	acteristics	· · · ·				
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 5 A; T _j = 25 °C	-	-	161	mΩ
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C	-	116	137	mΩ
		V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12;</u> Fig. 13	-	128	150	mΩ
Dynamic cl	haracteristics	· · · · ·	I			
Q _{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; V_{DS} = 44 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 14$	-	2.8	-	nC
Avalanche	ruggedness	· · · · ·				
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 5.5 A; V_{sup} ≤ 55 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	22	mJ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	4	D
2	D	drain		
3	S	source		G
4	D	drain	L1 L2 L3 SC-73 (SOT223)	mbb076 S

6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUK98150-55A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223				
BUK98150-55A/CU	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223				

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK98150-55A	915055A
BUK98150-55A/CU	915055

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	55	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	55	V
V _{GS}	gate-source voltage		-15	15	V
P _{tot}	total power dissipation	T _{sp} = 25 °C; <u>Fig. 1</u>	-	8	W
I _D	drain current	T _{sp} = 25 °C; V _{GS} = 5 V; <u>Fig. 2; Fig. 3</u>	-	5.5	А
		T _{sp} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	-	3	А
I _{DM}	peak drain current	T_{sp} = 25 °C; pulsed; $t_p \le 10 \ \mu s$; Fig. 3	-	22	А

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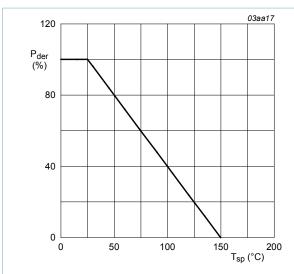
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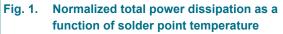
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Symbol	Parameter	Conditions		Min	Мах	Unit
T _{stg}	storage temperature			-55	150	°C
Tj	junction temperature			-55	150	°C
Source-drai	in diode					
I _S	source current	T _{sp} = 25 °C		-	5.5	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{sp} = 25 \ ^\circ C$		-	22	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 5.5 A; V_{sup} ≤ 55 V; R_{GS} = 50 Ω; V_{GS} = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	22	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy	Fig. 4	[1][2][3]	[4]	-	J

[1]

- Value not quoted. Repetitive rating defined in avalanche rating figure. Single-pulse avalanche rating limited by maximum junction temperature of 150 °C. [2]
- [3] Repetitive avalanche rating limited by an average junction temperature of 145 °C.
- Refer to application note AN10273 for further information. [4]





$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

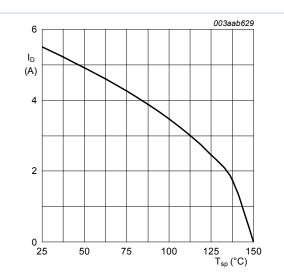


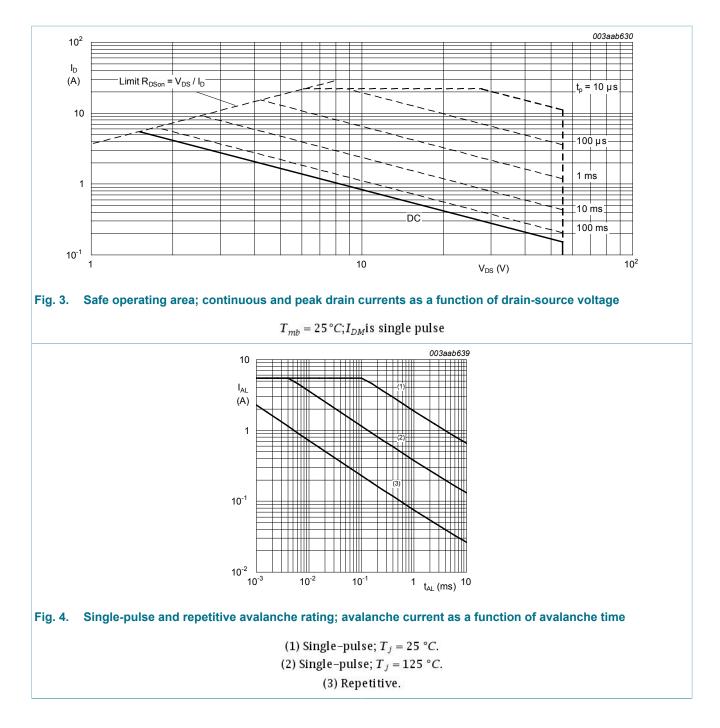
Fig. 2. Continuous drain current as a function of solder point temperature

 $V_{GS} \ge 5V$

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9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	<u>Fig. 5</u>	-	-	15	K/W

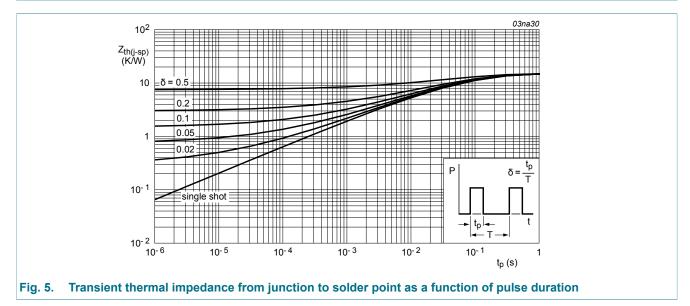
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		-	120	-	K/W



10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·				_
V _{(BR)DSS}	drain-source	I _D = 0.25 mA; V _{GS} = 0 V; T _j = -55 °C	50	-	-	V
	breakdown voltage	I_D = 0.25 mA; V_{GS} = 0 V; T_j = 25 °C	55	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 11	1	1.5	2	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 150 °C; Fig. 11	0.6	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 11	-	-	2.3	V
I _{DSS}	drain leakage current	V_{DS} = 55 V; V_{GS} = 0 V; T_j = 25 °C	-	0.05	10	μA
		V_{DS} = 55 V; V_{GS} = 0 V; T_j = 150 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 15 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -15 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 150 °C; Fig. 12; Fig. 13	-	-	276	mΩ
		V_{GS} = 4.5 V; I _D = 5 A; T _j = 25 °C	-	-	161	mΩ
		V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C	-	116	137	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12;</u> <u>Fig. 13</u>	-	128	150	mΩ
Dynamic cl	haracteristics		II			
Q _{G(tot)}	total gate charge	$I_D = 5 A; V_{DS} = 44 V; V_{GS} = 5 V;$	-	5.3	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 14</u>	-	1	-	nC
Q _{GD}	gate-drain charge	-	-	2.8	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz; T _j = 25 °C; <u>Fig. 15</u>	-	240	320	pF
C _{oss}	output capacitance		-	53	64	pF
C _{rss}	reverse transfer capacitance		-	40	55	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R _L = 3.3 Ω; V _{GS} = 5 V;	-	8	-	ns
t _r	rise time	R _{G(ext)} = 10 Ω; T _j = 25 °C	-	57	-	ns
t _{d(off)}	turn-off delay time		-	16	-	ns
t _f	fall time	-	-	13	-	ns
Source-dra	in diode	-	I I	1		
V _{SD}	source-drain voltage	I_{S} = 5 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 5 A; dI _S /dt = -100 A/μs;	-	24	-	ns
Qr	recovered charge	V _{GS} = -10 V; V _{DS} = 30 V; T _j = 25 °C	-	30	-	nC

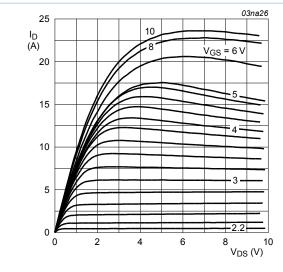


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

 $T_j = 25^{\circ}C; t_p = 300 \mu s$

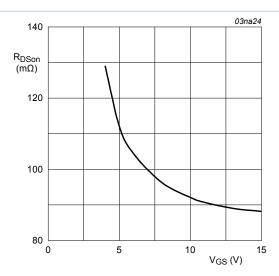


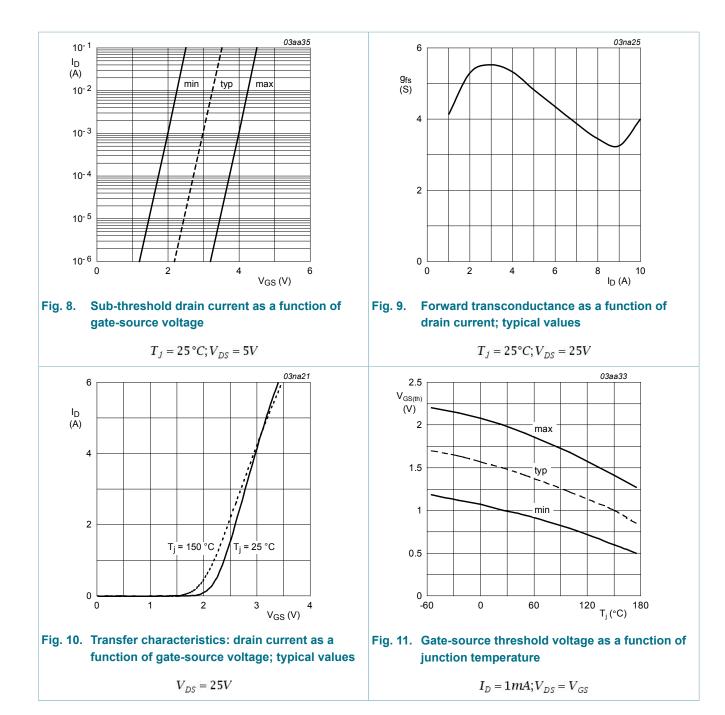
Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 5A$

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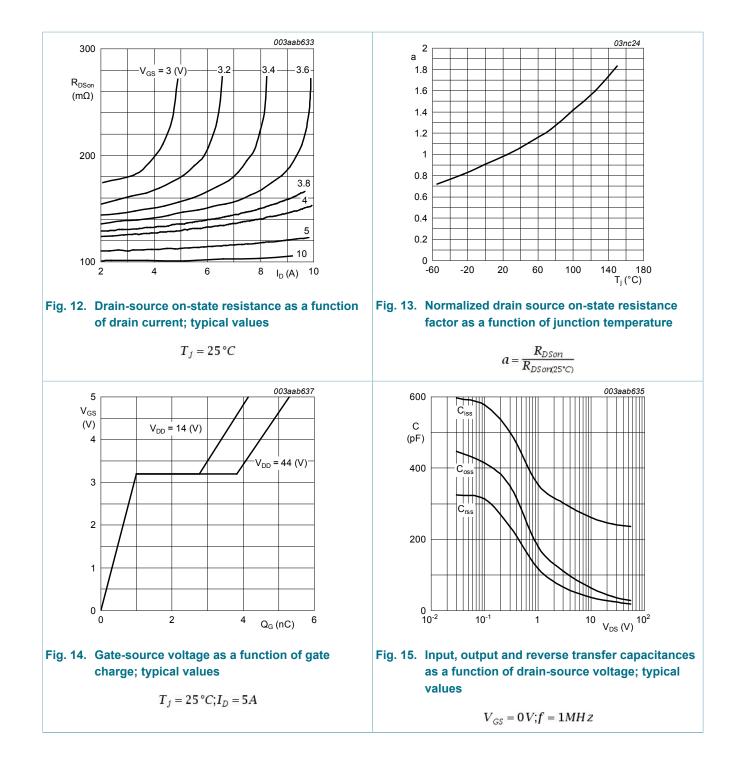
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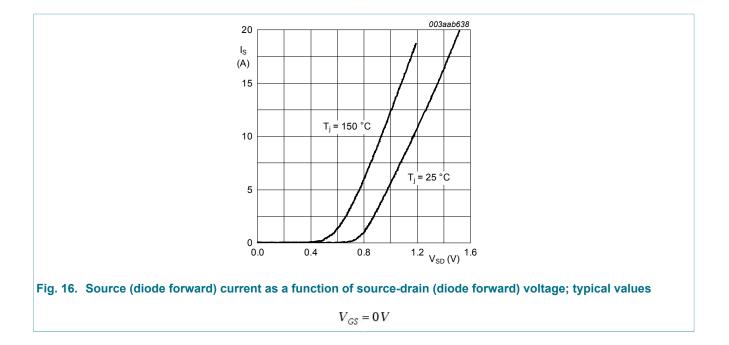
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11. Package outline

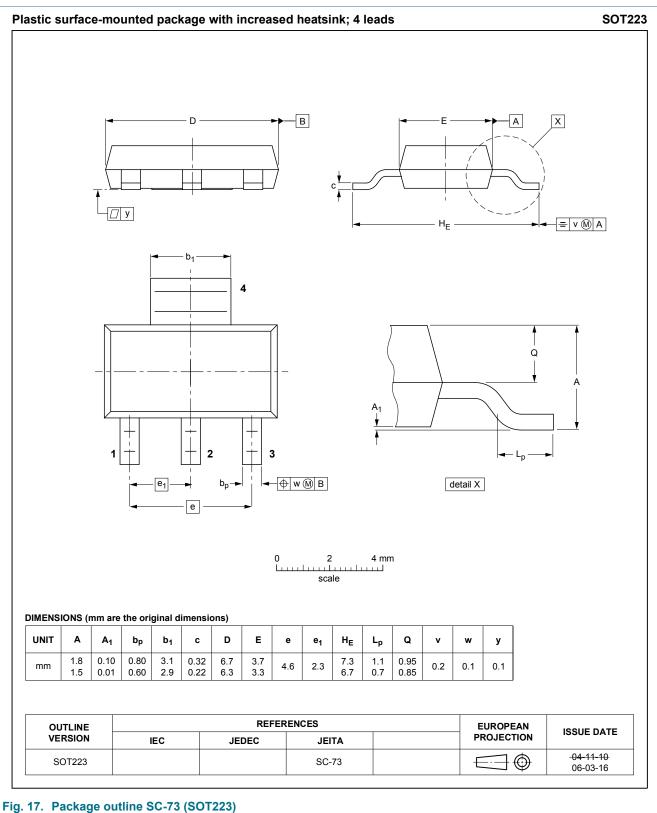


 FIG. 17. Package outline SC-73 (SO1223)

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12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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